

# Kerstin Volz

## List of Publications by Year in descending order

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170  
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172207

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173  
docs citations

173  
times ranked

3080  
citing authors

#	ARTICLE	IF	CITATIONS
1	Selective Effects of the Host Matrix in Hydrogenated InGaAsN Alloys: Toward an Integrated Matrix/Defect Engineering Paradigm. <i>Advanced Functional Materials</i> , 2022, 32, 2108862.	7.8	0
2	Room-temperature laser operation of a (Ga,In)As/Ga(As,Bi)/(Ga,In)As W-type laser diode. <i>Electronics Letters</i> , 2022, 58, 70-72.	0.5	3
3	A Dry-Processed Al <sub>2</sub> O <sub>3</sub> /LiAlO <sub>2</sub> Coating for Stabilizing the Cathode/Electrolyte Interface in High-Ni NCM-Based All-Solid-State Batteries. <i>Advanced Materials Interfaces</i> , 2022, 9, 2101428.	1.9	24
4	Effect of growth interruption on Ga(N, As)/Ga(As, Sb)/Ga(N, As) type-II- $\omega$ -W-quantum well heterostructures. <i>Journal of Crystal Growth</i> , 2022, 582, 126501.	0.7	0
5	Separation of interface and substrate carrier dynamics at a heterointerface based on coherent phonons. <i>Physical Review B</i> , 2022, 105, .	1.1	1
6	Tracing Low Amounts of Mg in the Doped Cathode Active Material LiNiO <sub>2</sub> . <i>Journal of the Electrochemical Society</i> , 2022, 169, 030540.	1.3	15
7	Advanced Analytical Characterization of Interface Degradation in Ni-Rich NCM Cathode Co-Sintered with LTP Solid Electrolyte. <i>ACS Applied Energy Materials</i> , 2022, 5, 4651-4663.	2.5	10
8	White Light Generating Molecular Materials: Correlation Between the Amorphous/Crystalline Structure and Nonlinear Optical Properties. <i>ChemPhotoChem</i> , 2022, 6, .	1.5	0
9	Terahertz radiation from propagating acoustic phonons based on deformation potential coupling. <i>Optics Express</i> , 2022, 30, 23544.	1.7	2
10	Front Cover: White Light Generating Molecular Materials: Correlation Between the Amorphous/Crystalline Structure and Nonlinear Optical Properties ( <i>ChemPhotoChem</i> 6/2022). <i>ChemPhotoChem</i> , 2022, 6, .	1.5	0
11	Monitoring the thermally induced transition from sp <sup>3</sup> -hybridized into sp <sup>2</sup> -hybridized carbons. <i>Carbon</i> , 2021, 172, 214-227.	5.4	41
12	Angle-resolved STEM using an iris aperture: Scattering contributions and sources of error for the quantitative analysis in Si. <i>Ultramicroscopy</i> , 2021, 221, 113175.	0.8	8
13	Quantitative Characterization of Nanometer-Scale Electric Fields via Momentum-Resolved STEM. <i>Nano Letters</i> , 2021, 21, 2018-2025.	4.5	20
14	Comparison of carrier-recombination in Ga(As,Bi)/Ga(N,As)-type-II quantum wells and W-type heterostructures. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	6
15	Synthesis and Postprocessing of Single-Crystalline LiNi <sub>0.8</sub> Co <sub>0.15</sub> Al <sub>0.05</sub> O <sub>2</sub> for Solid-State Lithium-Ion Batteries with High Capacity and Long Cycling Stability. <i>Chemistry of Materials</i> , 2021, 33, 2624-2634.	3.2	38
16	In-situ biasing and temperature influence on the electric fields across GaAs based p-n junction via 4D STEM. <i>Microscopy and Microanalysis</i> , 2021, 27, 2238-2239.	0.2	0
17	A robust technique to image all elements in LiNiO <sub>2</sub> cathode active material by 4D-STEM. <i>Microscopy and Microanalysis</i> , 2021, 27, 1446-1449.	0.2	0
18	Decomposition behavior of III/V semiconductor precursor gases in a closed gas cell in-situ TEM holder observed by mass spectrometry. <i>Microscopy and Microanalysis</i> , 2021, 27, 2220-2222.	0.2	0

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19	Formation mechanism of dominant kinks in GaP nanowires grown in an in-situ (S)TEM gas cell holder investigated by SPED and SNBED. <i>Microscopy and Microanalysis</i> , 2021, 27, 2228-2230.	0.2	0
20	Quantitative characterization of nanometer-scale electric fields via momentum-resolved STEM. <i>Microscopy and Microanalysis</i> , 2021, 27, 2206-2207.	0.2	0
21	Characterization of III/V Semiconductors on Silicon by Analyzing 4D-STEM Data with Convolutional Neural Networks. <i>Microscopy and Microanalysis</i> , 2021, 27, 450-452.	0.2	0
22	Analyzing Nanometer-Thin Cathode Particle Coatings for Lithium-Ion Batteries—The Example of TiO <sub>2</sub> on NCM622. <i>ACS Applied Energy Materials</i> , 2021, 4, 7168-7181.	2.5	11
23	Quantification of low-Z elements by energy-filtered scanning transmission electron microscopy. <i>Microscopy and Microanalysis</i> , 2021, 27, 1528-1529.	0.2	0
24	Optimization of imaging conditions for composition determination by annular dark field STEM. <i>Ultramicroscopy</i> , 2021, 230, 113387.	0.8	2
25	Stabilizing the Cathode/Electrolyte Interface Using a Dry-Processed Lithium Titanate Coating for All-Solid-State Batteries. <i>Chemistry of Materials</i> , 2021, 33, 6713-6723.	3.2	21
26	Amorphous Molecular Materials for Directed Supercontinuum Generation. <i>ChemPhotoChem</i> , 2021, 5, 1033-1041.	1.5	11
27	Optimized atomic layer deposition of homogeneous, conductive Al <sub>2</sub> O <sub>3</sub> coatings for high-nickel NCM containing ready-to-use electrodes. <i>Physical Chemistry Chemical Physics</i> , 2021, 23, 6725-6737.	1.3	20
28	Understanding the formation of antiphase boundaries in layered oxide cathode materials and their evolution upon electrochemical cycling. <i>Matter</i> , 2021, 4, 3953-3966.	5.0	20
29	Revealing the Significance of Catalytic and Alkyl Exchange Reactions during GaAs and GaP Growth by Metal Organic Vapor Phase Epitaxy. <i>ACS Omega</i> , 2021, 6, 28229-28241.	1.6	1
30	Reaction of Li <sub>1.3</sub> Al <sub>0.3</sub> Ti <sub>1.7</sub> (PO <sub>4</sub> ) <sub>3</sub> and LiNi <sub>0.6</sub> Co <sub>0.2</sub> Mn <sub>0.2</sub> O <sub>2</sub> in Co-Sintered Composite Cathodes for Solid-State Batteries. <i>ACS Applied Materials &amp; Interfaces</i> , 2021, 13, 47488-47498.	4.0	20
31	Amorphous Molecular Materials for Directed Supercontinuum Generation. <i>ChemPhotoChem</i> , 2021, 5, 1029.	1.5	2
32	Type-II GaAs <sub>1-x</sub> Bi <sub>x</sub> /GaN <sub>y</sub> As <sub>1-y</sub> "W" quantum wells for strain-compensated GaAs-based telecom lasers. , 2021, , .		0
33	Anomalous Angle-Dependent Magnetotransport Properties of Single InAs Nanowires. <i>Nano Letters</i> , 2020, 20, 618-624.	4.5	7
34	Giant Bowing of the Bandgap and Spin-Orbit Splitting in GaP <sub>1-x</sub> Bi <sub>x</sub> Dilute Bismide Alloys. , 2020, , .		0
35	Decomposition Behavior of III/V Semiconductor Precursor Gases in In-situ TEM MOVPE Investigations Observed by Mass Spectrometry. <i>Microscopy and Microanalysis</i> , 2020, 26, 2408-2409.	0.2	0
36	Quantitative Simulation of Four-dimensional STEM Datasets. <i>Microscopy and Microanalysis</i> , 2020, 26, 250-251.	0.2	0

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37	Influence of plasmon excitations on atomic-resolution quantitative 4D scanning transmission electron microscopy. <i>Scientific Reports</i> , 2020, 10, 17890.	1.6	21
38	<i>In Situ</i> Monitoring of Thermally Induced Effects in Nickel-Rich Layered Oxide Cathode Materials at the Atomic Level. <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 57047-57054.	4.0	16
39	Measuring Interatomic Bonding and Charge Redistributions in Defects by Combining 4D-STEM and STEM Multislice Simulations. <i>Microscopy and Microanalysis</i> , 2020, 26, 452-454.	0.2	1
40	Self-Assembly of Nanovoids in Si Microcrystals Epitaxially Grown on Deeply Patterned Substrates. <i>Crystal Growth and Design</i> , 2020, 20, 2914-2920.	1.4	2
41	Ga(N,P) Growth on Si and Decomposition Studies of the Nâ€“P Precursor Di- <i>tert</i> -butylaminophosphane (DTBAP). <i>Organometallics</i> , 2020, 39, 1772-1781.	1.1	3
42	Epitaxial Growth and Structural Characterization of Ceria Deposited by Atomic Layer Deposition on High-Surface Porous Ytria-Stabilized Zirconia Thin Films. <i>Crystal Growth and Design</i> , 2020, 20, 2194-2201.	1.4	11
43	Progress in Sputter Growth of $\text{In}^2 \text{Ga}_2 \text{O}_3$ by Applying Pulsed-Mode Operation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020, 217, 1901009.	0.8	4
44	Visualization of Light Elements using 4D STEM: The Layered Rock Salt Phase Transition in $\text{LiNiO}_2$ Cathode Material. <i>Advanced Energy Materials</i> , 2020, 10, 2001026.	10.2	43
45	Advances in Epitaxial GaInP/GaAs/Si Triple Junction Solar Cells. , 2020, , .		3
46	Formation Mechanism of the Dominant Kinks in GaP Nanowires Grown in an In-situ (S)TEM Gas Cell Holder. <i>Microscopy and Microanalysis</i> , 2020, 26, 1432-1433.	0.2	0
47	Decomposition Mechanisms of Di- <i>tert</i> -butylaminoarsane (DTBAA). <i>Organometallics</i> , 2019, 38, 3181-3186.	1.1	4
48	Segregation at interfaces in (GaIn)As/Ga(AsSb)/(GaIn)As- quantum well heterostructures explored by atomic resolution STEM. <i>Journal of Crystal Growth</i> , 2019, 524, 125180.	0.7	7
49	MOVPE Growth and Device Applications of Ternary and Quaternary Dilute Bismide Alloys on GaAs Substrates. <i>Springer Series in Materials Science</i> , 2019, , 37-58.	0.4	2
50	Ge/SiGe parabolic quantum wells. <i>Journal Physics D: Applied Physics</i> , 2019, 52, 415105.	1.3	8
51	Composition determination for quaternary IIIâ€“V semiconductors by aberration-corrected STEM. <i>Ultramicroscopy</i> , 2019, 206, 112814.	0.8	2
52	Metalorganic vapor phase epitaxy growth and characterization of quaternary (Ga,In)(As,Bi) on GaAs substrates. <i>Journal of Applied Physics</i> , 2019, 126, 085707.	1.1	4
53	The Role of Intragranular Nanopores in Capacity Fade of Nickel-Rich Layered $\text{Li}(\text{Ni}_{1-x}\text{Co}_x\text{Mn}_y)\text{O}_2$ Cathode Materials. <i>ACS Nano</i> , 2019, 13, 10694-10704.	7.3	79
54	Bismuth surface segregation and disorder analysis of quaternary (Ga,In)(As,Bi)/InP alloys. <i>Journal of Applied Physics</i> , 2019, 126, 135705.	1.1	7

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55	Three-dimensional structure of antiphase domains in GaP on Si(001). Journal of Physics Condensed Matter, 2019, 31, 144001.	0.7	7
56	Ab-initio calculation of band alignments for opto-electronic simulations. AIP Advances, 2019, 9, 055328.	0.6	1
57	Advanced Electron Microscopy for III/V on Silicon Integration. Advanced Materials Interfaces, 2019, 6, 1801951.	1.9	22
58	Giant bowing of the band gap and spin-orbit splitting energy in GaP <sub>1-x</sub> Bi <sub>x</sub> dilute bismide alloys. Scientific Reports, 2019, 9, 6835.	1.6	11
59	Simultaneous determination of local thickness and composition for ternary III-V semiconductors by aberration-corrected STEM. Ultramicroscopy, 2019, 201, 49-57.	0.8	6
60	Composition determination of semiconductor alloys towards atomic accuracy by HAADF-STEM. Ultramicroscopy, 2019, 200, 84-96.	0.8	15
61	Detailed Identification of the Progression of Antiphase Boundaries in GaP/Si(001). ECS Transactions, 2019, 93, 93-96.	0.3	0
62	Monolithic integration of lattice-matched Ga(NAsP)-based laser structures on CMOS-compatible Si (001) wafers for Si-photonics applications. Semiconductors and Semimetals, 2019, , 201-227.	0.4	2
63	Effect of the interface morphology on the lateral electron transport in (001) GaP/Si heterostructures. Journal of Applied Physics, 2019, 126, .	1.1	3
64	Coherent optical and acoustic phonons generated at lattice-matched GaP/Si(001) heterointerfaces. Journal of Physics Condensed Matter, 2019, 31, 094003.	0.7	8
65	Correlation of optical properties and interface morphology in type-II semiconductor heterostructures. Journal of Physics Condensed Matter, 2019, 31, 014001.	0.7	3
66	Single- and dual-variant atomic ordering in GaAsP compositionally graded buffers on GaP and Si substrates. Journal of Crystal Growth, 2019, 506, 61-70.	0.7	6
67	Ab initio calculations of the concentration dependent band gap reduction in dilute nitrides. Physical Review B, 2018, 97, .	1.1	9
68	Tailoring the diameter of electrospun layered perovskite nanofibers for photocatalytic water splitting. Journal of Materials Chemistry A, 2018, 6, 1971-1978.	5.2	17
69	Composition determination of multinary III/V semiconductors via STEM HAADF multislice simulations. Ultramicroscopy, 2018, 185, 15-20.	0.8	4
70	Influence of the atom source operating parameters on the structural and optical properties of In <sub>x</sub> Ga <sub>1-x</sub> N nanowires grown by plasma-assisted molecular beam epitaxy. Journal of Applied Physics, 2018, 124, 165703.	1.1	3
71	Investigation of Fluorine and Nitrogen as Anionic Dopants in Nickel-Rich Cathode Materials for Lithium-Ion Batteries. ACS Applied Materials & Interfaces, 2018, 10, 44452-44462.	4.0	63
72	Second-harmonic generation as a probe for structural and electronic properties of buried GaP/Si(001) interfaces. Journal of Physics Condensed Matter, 2018, 30, 484001.	0.7	5

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73	Direct Growth of III-V/Silicon Triple-Junction Solar Cells With 19.7% Efficiency. IEEE Journal of Photovoltaics, 2018, 8, 1590-1595.	1.5	48
74	Atomic-scale 3D reconstruction of antiphase boundaries in GaP on (001) silicon by STEM. Micron, 2018, 114, 32-41.	1.1	5
75	GaP-interlayer formation on epitaxial GaAs(100) surfaces in MOVPE ambient. Journal of Crystal Growth, 2017, 464, 2-7.	0.7	5
76	Local Bi ordering in MOVPE grown Ga(As,Bi) investigated by high resolution scanning transmission electron microscopy. Applied Materials Today, 2017, 6, 22-28.	2.3	21
77	(GaIn)(NAs) growth using di-tertiary-butyl-arsano-amine (DTBAA). Journal of Crystal Growth, 2017, 467, 132-136.	0.7	13
78	MOVPE Grown Gallium Phosphide-Silicon Heterojunction Solar Cells. IEEE Journal of Photovoltaics, 2017, 7, 502-507.	1.5	54
79	MOVPE growth of Ga(PBi) on GaP and GaP on Si with Bi fractions up to 8%. Journal of Crystal Growth, 2017, 463, 151-155.	0.7	10
80	Quantitative atomic resolution at interfaces: Subtraction of the background in STEM images with the example of (Ga,In)P/GaAs structures. Journal of Applied Physics, 2017, 121, .	1.1	9
81	GaAs <sub>1-x</sub> Bix/GaNyAs <sub>1-y</sub> type-II quantum wells: novel strain-balanced heterostructures for GaAs-based near- and mid-infrared photonics. Scientific Reports, 2017, 7, 46371.	1.6	23
82	Orientation relationships of Mn <sub>0.75</sub> Ga <sub>0.25</sub> As crystallites on and within GaAs determined by scanning nano beam electron diffraction. Crystal Research and Technology, 2017, 52, 1600261.	0.6	0
83	Influence of surface relaxation of strained layers on atomic resolution ADF imaging. Ultramicroscopy, 2017, 181, 8-16.	0.8	17
84	Microstructural study of codeposited pentacene:perfluoropentacene grown on KCl by TEM techniques. Journal of Crystal Growth, 2017, 471, 29-36.	0.7	3
85	STEMsalabim: A high-performance computing cluster friendly code for scanning transmission electron microscopy image simulations of thin specimens. Ultramicroscopy, 2017, 177, 91-96.	0.8	50
86	Atomic structure of W <sup>TM</sup> -type quantum well heterostructures investigated by aberration-corrected STEM. Journal of Microscopy, 2017, 268, 259-268.	0.8	8
87	Surface relaxation of strained Ga(P,As)/GaP heterostructures investigated by HAADF STEM. Journal of Microscopy, 2017, 268, 239-247.	0.8	11
88	Formation and Structural Diversity of Organo-Functionalized Tin-Silver Selenide Clusters. Chemistry - A European Journal, 2017, 23, 15607-15611.	1.7	13
89	Sub-picosecond acoustic pulses at buried GaP/Si interfaces. Applied Physics Letters, 2017, 111, .	1.5	12
90	<i>In Situ</i> Thermal Annealing Transmission Electron Microscopy (TEM) Investigation of III/V Semiconductor Heterostructures Using a Setup for Safe Usage of Toxic and Pyrophoric Gases. Microscopy and Microanalysis, 2017, 23, 751-757.	0.2	9

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91	On The Effects of Column Occupancy and Static Atomic Disorder on the Analysis of Chemical Ordering in Ga(P(1-x)Bi <sub>x</sub> ) Compounds. <i>Microscopy and Microanalysis</i> , 2017, 23, 1474-1475.	0.2	1
92	Three dimensional reconstruction of InGaN nanodisks in GaN nanowires: Improvement of the nanowire sample preparation to avoid missing wedge effects. <i>Journal of Crystal Growth</i> , 2017, 475, 202-207.	0.7	3
93	MOVPE growth of (GaIn)As/Ga(AsSb)/(GaIn)As type-II heterostructures on GaAs substrate for near infrared laser applications. <i>Journal of Crystal Growth</i> , 2017, 464, 201-205.	0.7	10
94	Codeposited pentacene:perfluoropentacene grown on SiO <sub>2</sub> : A microstructural study by transmission electron microscopy. <i>Journal of Crystal Growth</i> , 2017, 458, 87-95.	0.7	4
95	Strain-balanced type-II superlattices on GaAs: Novel heterostructures for photonics and photovoltaics. , 2017, , .		1
96	Local sample thickness determination via scanning transmission electron microscopy defocus series. <i>Journal of Microscopy</i> , 2016, 262, 171-177.	0.8	14
97	Thermomigration and Soret effect in Na <sub>x</sub> CoO <sub>2</sub> as thermoelectric material: Preparation and characterization of sodium cobaltate thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 1284-1295.	0.8	8
98	Coherent phonon spectroscopy characterization of electronic bands at buried semiconductor heterointerfaces. <i>Applied Physics Letters</i> , 2016, 108, 051607.	1.5	23
99	Preparation and Loading Process of Single Crystalline Samples into a Gas Environmental Cell Holder for In Situ Atomic Resolution Scanning Transmission Electron Microscopic Observation. <i>Microscopy and Microanalysis</i> , 2016, 22, 515-519.	0.2	10
100	Correlation of the nanostructure with optoelectronic properties during rapid thermal annealing of Ga(NAsP) quantum wells grown on Si(001) substrates. <i>Journal of Applied Physics</i> , 2016, 119, 025705.	1.1	6
101	Efficient nitrogen incorporation in GaAs using novel metal organic As <sup>III</sup> N precursor di-tertiary-butyl-arsano-amine (DTBAA). <i>Journal of Crystal Growth</i> , 2016, 439, 19-27.	0.7	17
102	FIB Plan View Preparation and Electron Tomography of Ga-Containing Droplets Induced by Melt-Back Etching in Si. <i>Microscopy and Microanalysis</i> , 2016, 22, 131-139.	0.2	3
103	Pyramidal Structure Formation at the Interface between III/V Semiconductors and Silicon. <i>Chemistry of Materials</i> , 2016, 28, 3265-3275.	3.2	37
104	Novel nitrogen/gallium precursor [Ga(bdma)H <sub>2</sub> ] for MOVPE. <i>Journal of Crystal Growth</i> , 2016, 454, 173-179.	0.7	3
105	Surface Chemistry of tert-Butylphosphine (TBP) on Si(001) in the Nucleation Phase of Thin-Film Growth. <i>Chemistry - A European Journal</i> , 2016, 22, 14920-14928.	1.7	10
106	Materials characterisation by angle-resolved scanning transmission electron microscopy. <i>Scientific Reports</i> , 2016, 6, 37146.	1.6	33
107	Microstructural Analysis of Perfluoropentacene Films on Graphene and Graphite: Interface-Mediated Alignment and Island Formation. <i>Crystal Growth and Design</i> , 2016, 16, 6941-6950.	1.4	6
108	Optical gain in GaAsBi/GaAs quantum well diode lasers. <i>Scientific Reports</i> , 2016, 6, 28863.	1.6	61

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109	A highly efficient directional molecular white-light emitter driven by a continuous-wave laser diode. <i>Science</i> , 2016, 352, 1301-1304.	6.0	120
110	Influence of spatial and temporal coherences on atomic resolution high angle annular dark field imaging. <i>Ultramicroscopy</i> , 2016, 169, 1-10.	0.8	20
111	Direct investigation of (sub-) surface preparation artifacts in GaAs based materials by FIB sectioning. <i>Ultramicroscopy</i> , 2016, 163, 19-30.	0.8	11
112	Interface morphology and composition of Ga(NAsP) quantum well structures for monolithically integrated LASERs on silicon substrates. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 075108.	1.3	18
113	Impedance spectroscopic study of the charge transfer resistance at the interface between a LiNi <sub>0.5</sub> Mn <sub>1.5</sub> O <sub>4</sub> high-voltage cathode film and a LiNbO <sub>3</sub> coating film. <i>Solid State Ionics</i> , 2016, 287, 8-12.	1.3	35
114	MOVPE growth studies of Ga(NAsP)/(BGa)(AsP) multi quantum well heterostructures (MQWH) for the monolithic integration of laser structures on (001) Si-substrates. <i>Journal of Crystal Growth</i> , 2016, 438, 63-69.	0.7	19
115	Quantification of Bi distribution in MOVPE-grown Ga(AsBi) via HAADF STEM. <i>Journal of Crystal Growth</i> , 2016, 433, 89-96.	0.7	11
116	In situ Observation of Annealing Effects in Ga(NAsP) Multi Quantum Well Structures. <i>Microscopy and Microanalysis</i> , 2015, 21, 957-958.	0.2	0
117	Atomically ordered (Mn,Ga)As crystallites on and within GaAs. <i>Crystal Research and Technology</i> , 2015, 50, 967-973.	0.6	1
118	Quantitative Determination of Chemical Composition of Multinary III/V Semiconductors With Sublattice Resolution Using Aberration Corrected HAADF-STEM. <i>Microscopy and Microanalysis</i> , 2015, 21, 2081-2082.	0.2	0
119	Determination of type-I band offsets in GaBi <sub>x</sub> As <sub>1-x</sub> quantum wells using polarisation-resolved photovoltage spectroscopy and 12-band k.p calculations. <i>Semiconductor Science and Technology</i> , 2015, 30, 094009.	1.0	29
120	Charge Transfer across the Interface between LiNi <sub>0.5</sub> Mn <sub>1.5</sub> O <sub>4</sub> High-Voltage Cathode Films and Solid Electrolyte Films. <i>Journal of the Electrochemical Society</i> , 2015, 162, A754-A759.	1.3	20
121	Metastable cubic zinc-blende III/V semiconductors: Growth and structural characteristics. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2015, 61, 46-62.	1.8	16
122	Growth of III/Vs on Silicon. , 2015, , 1249-1300.		8
123	Interface engineering and characterization at the atomic-scale of pure and mixed ion layer gas reaction buffer layers in chalcopyrite thin-film solar cells. <i>Progress in Photovoltaics: Research and Applications</i> , 2015, 23, 705-716.	4.4	20
124	Bipolar Electric-Field Enhanced Trapping and Detrapping of Mobile Donors in BiFeO <sub>3</sub> Memristors. <i>ACS Applied Materials &amp; Interfaces</i> , 2014, 6, 19758-19765.	4.0	84
125	Comparison of Direct Growth and Wafer Bonding for the Fabrication of GaInP/GaAs Dual-Junction Solar Cells on Silicon. <i>IEEE Journal of Photovoltaics</i> , 2014, 4, 620-625.	1.5	98
126	LiNi <sub>0.5</sub> Mn <sub>1.5</sub> O <sub>4</sub> Thin-Film Cathodes on Gold-Coated Stainless Steel Substrates: Formation of Interlayers and Electrochemical Properties. <i>Electrochimica Acta</i> , 2014, 133, 146-152.	2.6	16



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127	Microstructural Characterization of Organic Heterostructures by (Transmission) Electron Microscopy. <i>Crystal Growth and Design</i> , 2014, 14, 3010-3014.	1.4	3
128	Investigation of the microstructure of metallic droplets on Ga(AsBi)/GaAs. <i>Journal of Crystal Growth</i> , 2014, 408, 71-77.	0.7	33
129	Structural characteristics of gallium metal deposited on Si (001) by MOCVD. <i>Journal of Crystal Growth</i> , 2014, 405, 102-109.	0.7	30
130	Annealing effects on the composition and disorder of Ga(N,As,P) quantum wells on silicon substrates for laser application. <i>Journal of Crystal Growth</i> , 2014, 402, 169-174.	0.7	9
131	Simultaneous Quantification of Indium and Nitrogen Concentration in InGaNAs Using HAADF-STEM. <i>Microscopy and Microanalysis</i> , 2014, 20, 1740-1752.	0.2	20
132	Migration-enhanced epitaxy of thin GaAsBi layers. <i>Lithuanian Journal of Physics</i> , 2014, 54, 125-129.	0.1	8
133	Carrier-phonon Dynamics at Buried Interface of GaP/Si(001)., 2014, , .		0
134	Quantitative chemical evaluation of dilute GaNAs using ADF STEM: Avoiding surface strain induced artifacts. <i>Ultramicroscopy</i> , 2013, 129, 1-9.	0.8	29
135	In(SAr) <sub>3</sub> As a Building Block for 3D and Helical Coordination Polymers. <i>Crystal Growth and Design</i> , 2013, 13, 1252-1259.	1.4	14
136	Band structure properties of (BGa)P semiconductors for lattice matched integration on (001) silicon. , 2013, , .		3
137	Monolithic integration of high electron mobility InAs-based heterostructure on exact (001) Silicon using a GaSb/GaP accommodation layer. <i>Applied Physics Letters</i> , 2012, 101, 142111.	1.5	29
138	Monolithic integration of III/V devices on Si(001)., 2012, , .		0
139	Growth study of nonpolar Zn <sub>1-x</sub> Mg <sub>x</sub> O epitaxial films on a-plane bulk ZnO by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2012, 101, 122106.	1.5	4
140	Scanning transmission electron microscopy strain measurement from millisecond frames of a direct electron charge coupled device. <i>Applied Physics Letters</i> , 2012, 101, 212110.	1.5	63
141	Strain Measurement in Semiconductor Heterostructures by Scanning Transmission Electron Microscopy. <i>Microscopy and Microanalysis</i> , 2012, 18, 995-1009.	0.2	62
142	Quantitative HAADF-studies of GaP/Si-interfaces. <i>Microscopy and Microanalysis</i> , 2012, 18, 352-353.	0.2	0
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